TEXAS INSTRUMENTS

TS5A12301E

SCES707C – AUGUST 2008 – REVISED DECEMBER 2016

TS5A12301E IEC Level 4 ESD-protected 0.75-Ω SPDT Analog Switch With 1.8-V Compatible Input Logic

1 Features

- Low ON-State Resistance (0.75 Ω)
- Low Charge Injection
- Excellent ON-State Resistance Matching
- Isolation in Power-Down Mode, V_{CC} = 0
- Specified Break-Before-Make Switching
- 2.25-V to 5.5-V Power Supply (V_{CC})
- 6-MΩ Input Pulldown Allows Control Input (IN) to Be Unconnected
- 1.8-V Compatible Control Input Threshold Independent of V_{CC}
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22
  - 3000-V Human-Body Model (A114-B, Class II)
  - 1000-V Charged-Device Model (C101)
- ESD Performance COM Port to GND
  - 8000-V Human-Body Model (A114-B, Class II)
  - ±8-kV Contact Discharge (IEC 61000-4-2)
  - ±15-kV Air-Gap Discharge (IEC 61000-4-2)

2 Applications

- Cell Phones
- PDAs
- Portable Instrumentation
- MP3 Players
- Portable Media Players

3 Description

The TS5A12301E device is a bidirectional, 1-channel, single-pole double-throw (SPDT) analog switch that is designed to operate from 2.25 V to 5.5 V. The device offers a low ON-state resistance with excellent channel-to-channel ON-state resistance matching and the break-before-make feature to prevent signal distortion during the transferring of a signal from one path to another.

The device has excellent total harmonic distortion (THD) performance and consumes very low power. These features make this device suitable for portable audio applications. The control input (IN) pin can be connected to low-voltage GPIOs, allowing it to be controlled by 1.8-V signals.

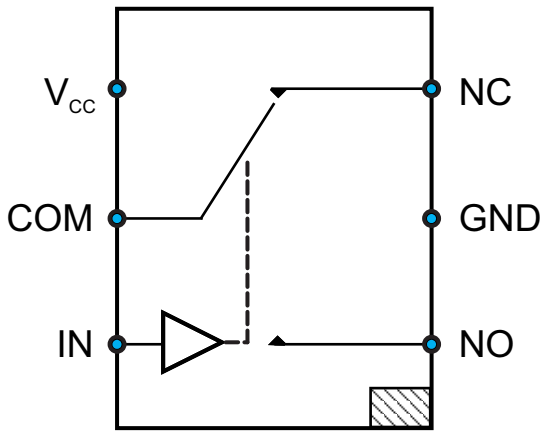
The TS5A12301E has ±15-kV air-gap discharge and ±8-kV contact discharge ESD protection for the COM port to GND, which makes it compliant with the IEC Level 4 ESD standard (IEC 61000-4-2).

Device Information(1)

PART NUMBER	PACKAGE	BODY SIZE (NOM)
TS5A12301E	DSBGA (6)	1.16 mm × 0.76 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Simplified Schematic



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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision B (April 2011) to Revision C **Page**

- Added *ESD Ratings* table, *Feature Description* section, *Device Functional Modes*, *Application and Implementation* section, *Power Supply Recommendations* section, *Layout* section, *Device and Documentation Support* section, and *Mechanical, Packaging, and Orderable Information* section. ... 1
- Changed all references of V+ pin to V_{CC} ... 1
- Deleted *Ordering Information* table; see POA at the end of the data sheet ... 1
- Deleted *Summary of Characteristics* table ... 1
- Changed continuous current parameter symbol from: I+ to: ICC ... 4
- Moved the on-state switch current and on-state peak switch current parameters to the *Recommended Operating Conditions* ... 4
- Changed RthetaJA value for the YFP package from: 154.2°C/W to: 123.4°C/W ... 5
- Removed analog signal range parameters from the *Electrical Characteristics* tables ... 5
- Deleted Leakage Current vs Temperature (V_{CC} = 5 V) graph ... 10
- Deleted Control Input Thresholds graph ... 10
- Added ohm symbols to Figure 18, Figure 19, and Figure 22 ... 14

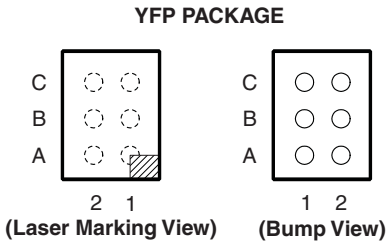
Changes from Revision A (December 2009) to Revision B **Page**

- Added Logic Diagram ... 1

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5 Pin Configuration and Functions

YFP Package
6-Pin DSBGA
Top View



Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
COM	B2	I/O	Common signal path
GND	B1	—	Ground
IN	A2	I	Digital control: High = COM connected to NO Low = COM connected to NC Floating = COM connected to NC
NC	C1	I/O	Normally closed signal path
NO	A1	I/O	Normally open signal path
V_{CC}	C2	—	Power supply

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6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)(2)

			MIN	MAX	UNIT
V_{CC}	Supply voltage(3)		–0.5	6.5	V
V_{NC}, V_{NO}, V_{COM}	Analog voltage(3)(4)		–0.5	V_{CC} + 0.5	V
I_{IK}	Analog port diode current	V_{CC} < V_{NC}, V_{NO}, V_{COM}, or V_{NC}, V_{NO}, V_{COM} < 0	–50	50	mA
V_{IN}	Digital input voltage(3)(5)		–0.5	6.5	V
I_{IK}	Digital input clamp current	V_I < 0	–50		mA
ICC, I_{GND}	Continuous current through V_{CC} or GND		–100	100	mA
T_{stg}	Storage temperature		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The algebraic convention (whereby the most negative value is a minimum and the most positive value is a maximum)
(3) All voltages are with respect to ground (unless otherwise specified).
(4) This value is limited to 5.5 V maximum.
(5) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±8000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	±8000	
		Contact discharge (IEC 61000-4-2)	8000	
		Air-gap discharge (IEC 61000-4-2)	15000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.25	5.5	V
V_{NC}, V_{NO}, V_{COM}	Analog voltage		0	V_{CC}	V
V_{IN}	Digital input voltage		0	5.5	V
I_{NC}, I_{NO}, I_{COM}	On-state switch current	V_{NC}, V_{NO}, V_{COM} = 0 to V_{CC}	–450	450	mA
	On-state peak switch current(1)	V_{NC}, V_{NO}, V_{COM} = 0 to V_{CC}	–700	700	
T_A	Operating temperature		–40	85	°C

(1) Pulse at 1-ms duration < 10% duty cycle

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6.4 Thermal Information

THERMAL METRIC[1]		TS5A12301E YFP (DSBGA) 6 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance[2]	123.4	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	1.9	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	37.6	°C/W
ψ_{JT}	Junction-to-top characterization parameter	0.4	°C/W
ψ_{JB}	Junction-to-board characterization parameter	37.7	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.
(2) The package thermal impedance is calculated in accordance with JESD 51-7.

6.5 Electrical Characteristics – 5-V Supply

V_{CC} = 4.5 V to 5.5 V and T_A = –40°C to 85°C (unless otherwise noted)[1]

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
ANALOG SWITCH							
r_{on}	ON-state resistance	V_{NO} or V_{NC} = 2.5 V, I_{COM} = –100 mA, and V_{CC} = 4.5 V (see Figure 12)	T_A = 25°C		0.5	0.75	Ω
			T_A = –40°C to 85°C			0.8	
Δr_{on}	ON-state resistance match between channels	V_{NO} or V_{NC} = 2.5 V, I_{COM} = –100 mA, and V_{CC} = 4.5 V (see Figure 12)	T_A = 25°C		0.05	0.1	Ω
			T_A = –40°C to 85°C			0.1	
$r_{on(flat)}$	ON-state resistance flatness	0 ≤ (V_{NO} or V_{NC}) ≤ V_{CC}, I_{COM} = –100 mA, V_{CC} = 4.5 V, and T_A = 25°C (see Figure 12)			0.15		Ω
		V_{NO} or V_{NC} = 1 V, 1.5 V, 2.5 V, I_{COM} = –100 mA, and V_{CC} = 4.5 V (see Figure 12)	T_A = 25°C		0.1	0.2	
			T_A = –40°C to 85°C			0.25	
$I_{NO(OFF)}$, $I_{NC(OFF)}$	NO and NC OFF leakage current	V_{NO} = 1 V, 4.5 V, V_{COM} = 4.5 V, 1 V, V_{NC} = open, or V_{NO} = 1 V, 4.5 V, V_{COM} = 4.5 V, 1 V, V_{NO} = open, and V_{CC} = 5.5 V (see Figure 13)	T_A = 25°C	–20	2	20	nA
			T_A = –40°C to 85°C	–100		100	
$I_{NO(PWROFF)}$, $I_{NC(PWROFF)}$	NO and NC PWROFF leakage current	V_{NO} or V_{NC} = 0 V to 5.5 V, V_{COM} = 5.5 V to 0 V, and V_{CC} = 0 V (see Figure 13)	T_A = 25°C	–10		10	µA
			T_A = –40°C to 85°C	–10		10	
$I_{NO(ON)}$	NC and NO ON leakage current	V_{NO} = 1 V, 4.5 V, V_{COM}, V_{NC} = open, or V_{NC} = 1 V, 4.5 V, V_{COM}, V_{NO} = open, and V_{CC} = 5.5 V (see Figure 14)	T_A = 25°C	–20	2	20	nA
			T_A = –40°C to 85°C	–200		200	
$I_{COM(ON)}$	COM ON leakage current	V_{COM} = 1 V, 4.5 V, V_{NO} and V_{NC} = open, or V_{COM} = 1 V, 4.5 V, V_{NO} or V_{NC} = open, and V_{CC} = 5.5 V (see Figure 14)	T_A = 25°C	–20	2	20	nA
			T_A = –40°C to 85°C	–200		200	
$I_{COM(PWROFF)}$	COM OFF leakage current	V_{NO} or V_{NC} = 0 V to 5.5 V, V_{COM} = 5.5 V to 0 V, and V_{CC} = 0 V (see Figure 13)	T_A = 25°C	–10		10	µA
			T_A = –40°C to 85°C	–10		10	
DIGITAL CONTROL INPUT (IN)							
V_{IH}	Input logic high	V_{CC} = 5.5 V and T_A = –40°C to 85°C		1.05		5.5	V
V_{IL}	Input logic low	V_{CC} = 5.5 V and T_A = –40°C to 85°C		0		0.65	V
I_{IH}, I_{IL}	Input leakage current	V_{IN} = 1.95 V or 0 V, V_{CC} = 5.5 V, and T_A = –40°C to 85°C		–0.05		0.5	µA
r_{IN}	Input resistance	V_{IN} = 1.95 V, V_{CC} = 5.5 V, and T_A = –40°C to 85°C			6		MΩ

(1) The algebraic convention (whereby the most negative value is a minimum and the most positive value is a maximum)

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Electrical Characteristics – 5-V Supply (continued)

V_{CC} = 4.5 V to 5.5 V and T_A = –40°C to 85°C (unless otherwise noted)(1)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
DYNAMIC							
t_{ON}	Turnon time	V_{COM} = V_{CC}, R_L = 50 Ω, C_L= 35 pF (see Figure 16)	V_{CC} = 5 V and T_A = 25°C		110	225	ns
			V_{CC} = 4.5 V and T_A = –40°C to 85°C			250	
t_{OFF}	Turnoff time	V_{COM} = V_{CC}, R_L = 50 Ω, C_L = 35 pF (see Figure 16)	V_{CC} = 5 V and T_A = 25°C		100	215	ns
			V_{CC} = 4.5 V and T_A = –40°C to 85°C			225	
t_{BBM}	Break-before-make time	V_{COM} = V_{CC}, R_L = 50 Ω, C_L = 35 pF (see Figure 17)	V_{CC} = 5 V and T_A = 25°C	1	10	15	ns
			V_{CC} = 4.5 V and T_A = –40°C to 85°C	1		20	
Q_C	Charge injection	V_{GEN} = 0, R_{GEN} = 0, C_L = 1 nF, V_{CC} = 5 V, and T_A = 25°C (see Figure 21)			97		pC
$C_{NO(OFF)}$	NO OFF capacitance	V_{NC} or V_{NO} = V_{CC} or GND, switch OFF, V_{CC} = 5 V, and T_A = 25°C (see Figure 15)			28		pF
$C_{NC(ON)}$, $C_{NO(ON)}$	NC and NO ON capacitance	V_{NC} or V_{NO} = V_{CC} or GND, switch ON, V_{CC} = 5 V, and T_A = 25°C (see Figure 15)			112		pF
$C_{COM(ON)}$	COM ON capacitance	V_{COM} = V_{CC} or GND, switch ON, V_{CC} = 5 V, and T_A = 25°C (see Figure 15)			112		pF
C_I	Digital input capacitance	V_{IN} = V_{CC} or GND, and T_A = 25°C (see Figure 15)			3		pF
BW	Bandwidth	R_L = 50 Ω, switch ON, V_{CC} = 5 V, and T_A = 25°C (see Figure 18)			55		MHz
O_{ISO}	OFF isolation	R_L = 50 Ω, f = 1 MHz, V_{CC} = 5 V, and T_A = 25°C (see Figure 19)			–63		dB
X_{TALK}	Crosstalk	R_L = 50 Ω, f = 1 MHz, V_{CC} = 5 V, and T_A = 25°C (see Figure 20)			–63		dB
THD	Total harmonic distortion	R_L = 600 Ω, C_L = 50 pF, f = 20 Hz to 20 kHz, V_{CC} = 5 V, and T_A = 25°C (see Figure 22)			0.003 %		
SUPPLY							
ICC	Positive supply current	V_{IN} = V_{CC} or GND, V_{CC} = 5.5 V, and T_A = –40°C to 85°C				10	µA

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6.6 Electrical Characteristics – 3.3-V Supply

V_{CC} = 3 V to 3.6 V and T_A = –40°C to 85°C (unless otherwise noted)(1)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
ANALOG SWITCH							
r_{on}	ON-state resistance	V_{NO} or V_{NC} = 2 V, I_{COM} = –100 mA, switch ON, and V_{CC} = 3 V (see Figure 12)	T_A = 25°C		0.75	0.9	Ω
			T_A = –40°C to 85°C			1.2	
Δr_{on}	ON-state resistance match between channels	V_{NO} or V_{NC} = 2 V, 0.8 V, I_{COM} = –100 mA, switch ON, and V_{CC} = 3 V (see Figure 12)	T_A = 25°C		0.1	0.15	Ω
			T_A = –40°C to 85°C			0.15	
$r_{on(flat)}$	ON-state resistance flatness	0 ≤ (V_{NO} or V_{NC}) ≤ V_{CC}, I_{COM} = –100 mA, switch ON, V_{CC} = 3 V, and T_A = 25°C (see Figure 12)			0.2		Ω
		V_{NO} or V_{NC} = 0.8 V, 2 V, I_{COM} = –100 mA, switch ON, and V_{CC} = 3 V (see Figure 12)	T_A = 25°C		0.1	0.2	
			T_A = –40°C to 85°C			0.3	
$I_{NO(OFF)}$, $I_{NC\ (OFF)}$	NO and NC OFF leakage current	V_{NO} = 1 V, 3 V, V_{COM} = 3 V, 1 V, V_{NC} = open, or V_{NC} = 1 V, 3 V, V_{COM} = 3 V, 1 V, V_{NO} = open, switch OFF, and V_{CC} = 3.6 V (see Figure 13)	T_A = 25°C	–20	2	20	nA
			T_A = –40°C to 85°C	–50		50	
$I_{NO(PWROFF)}$, $I_{NC\ (PWROFF)}$	NO and NC PWROFF leakage current	V_{NO} or V_{NC} = 0 V to 3.6 V, V_{COM} = 3.6 V to 0 V, switch OFF, and V_{CC} = 0 V (see Figure 13)	T_A = 25°C	–10		10	µA
			T_A = –40°C to 85°C	–10		10	
$I_{NO(ON)}$	NC and NO ON leakage current	V_{NO} = 1 V, 3 V, V_{NC} and V_{COM} = open, or V_{NC} = 1 V, 3 V, V_{NO} and V_{COM} = open, switch ON, and V_{CC} = 3.6 V (see Figure 14)	T_A = 25°C	–20	2	20	nA
			T_A = –40°C to 85°C	–100		100	
$I_{COM(ON)}$	COM ON leakage current	V_{COM} = 1 V, V_{NO} and V_{NC} = open, or V_{COM} = 3 V, V_{NO} and V_{NC} = open, and V_{CC} = 3.6 V (see Figure 14)	T_A = 25°C	–20	2	20	nA
			T_A = –40°C to 85°C	–100		100	
$I_{COM(PWROFF)}$	COM OFF leakage current	V_{NO} or V_{NC} = 0 V to 3.6 V, V_{COM} = 3.6 V to 0 V, and V_{CC} = 0 V (see Figure 13)	T_A = 25°C	–10		10	µA
			T_A = –40°C to 85°C	–10		10	
DIGITAL CONTROL INPUT (IN)							
V_{IH}	Input logic high	V_{CC} = 3.6 V and T_A = –40°C to 85°C		1.05		5.5	V
V_{IL}	Input logic low	V_{CC} = 3.6 V and T_A = –40°C to 85°C		0		0.65	V
I_{IH}, I_{IL}	Input leakage current	V_I = 1.95 V or 0 V, V_{CC} = 3.6 V, and T_A = –40°C to 85°C		–0.05		0.5	µA
r_{IN}	Input resistance	V_I = 1.95 V, V_{CC} = 3.6 V, and T_A = –40°C to 85°C			6		MΩ
DYNAMIC							
t_{ON}	Turnon time	V_{COM} = V_{CC}, R_L = 50 Ω, C_L= 35 pF (see Figure 16)	V_{CC} = 3.3 V and T_A = 25°C		72	175	ns
			V_{CC} = 3 V and T_A = –40°C to 85°C			185	
t_{OFF}	Turnoff time	V_{COM} = V_{CC}, R_L = 50 Ω, C_L = 35 pF (see Figure 16)	V_{CC} = 3.3 V and T_A = 25°C		105	165	ns
			V_{CC} = 3 V and T_A = –40°C to 85°C			170	
t_{BBM}	Break-before-make time	V_{COM} = V_{CC}, R_L = 50 Ω, C_L = 35 pF, (see Figure 17)	V_{CC} = 3.3 V and T_A = 25°C	1	16	30	ns
			V_{CC} = 3 V and T_A = –40°C to 85°C	1		35	
Q_C	Charge injection	V_{GEN} = 0, R_{GEN} = 0, C_L = 1 nF (see Figure 21)	V_{CC} = 3.3 V and T_A = 25°C		97		pC
$C_{NO(OFF)}$	NO OFF capacitance	V_{NO} = V_{CC} or GND, switch OFF, V_{CC} = 3.3 V, and T_A = 25°C (see Figure 15)			28		pF
$C_{NC(ON)}$, $C_{NO(ON)}$	NC and NO ON capacitance	V_{NC} or V_{NO} = V_{CC} or GND, switch ON, V_{CC} = 3.3 V, and T_A = 25°C (see Figure 15)			115		pF

(1) The algebraic convention (whereby the most negative value is a minimum and the most positive value is a maximum)

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Electrical Characteristics – 3.3-V Supply (continued)

V_{CC} = 3 V to 3.6 V and T_A = –40°C to 85°C (unless otherwise noted)(1)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$C_{COM(ON)}$	COM ON capacitance	V_{COM} = V_{CC} or GND, switch ON, V_{CC} = 3.3 V, and T_A = 25°C (see Figure 15)		115		pF
C_I	Digital input capacitance	V_{IN} = V_{CC} or GND, V_{CC} = 3.3 V, and T_A = 25°C (see Figure 15)		3		pF
BW	Bandwidth	R_L = 50 Ω, switch ON, V_{CC} = 3.3 V, and T_A = 25°C (see Figure 18)		54		MHz
O_{ISO}	OFF isolation	R_L = 50 Ω, f = 1 MHz, V_{CC} = 3.3 V, and T_A = 25°C (see Figure 19)		–63		dB
X_{TALK}	Crosstalk	R_L = 50 Ω, f = 1 MHz, V_{CC} = 3.3 V, and T_A = 25°C (see Figure 20)		–63		dB
THD	Total harmonic distortion	R_L = 600 Ω, C_L = 50 pF, f = 20 Hz to 20 kHz, V_{CC} = 3.3 V, and T_A = 25°C (see Figure 22)		0.004%		
SUPPLY						
ICC	Positive supply current	V_{IN} = 1.95 V or GND, V_{CC} = 3.6 V, and T_A = 25°C			10	µA

6.7 Electrical Characteristics – 2.5-V Supply

V_{CC} = 2.25 V to 2.75 V and T_A = –40°C to 85°C (unless otherwise noted)(1)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
ANALOG SWITCH							
r_{on}	ON-state resistance	V_{NO} or V_{NC} = 1.8 V, I_{COM} = –100 mA, switch ON, and V_{CC} = 2.25 V (see Figure 12)	T_A = 25°C		1.1	1.3	Ω
			T_A = –40°C to 85°C			1.6	
Δr_{on}	ON-state resistance match between channels	V_{NO} or V_{NC} = 1.8 V, 0.8 V, I_{COM} = –100 mA, switch ON, and V_{CC} = 2.25 V (see Figure 12)	T_A = 25°C		0.15	0.2	Ω
			T_A = –40°C to 85°C			0.2	
$r_{on(flat)}$	ON-state resistance flatness	0 ≤ (V_{NO} or V_{NC}) ≤ V_{CC}, I_{COM} = –100 mA, switch ON, V_{CC} = 2.25 V, and T_A = 25°C (see Figure 12)			0.4		Ω
		V_{NO} or V_{NC} = 0.8 V, 1 V, 1.8 V, I_{COM} = –100 mA, switch ON, and V_{CC} = 2.25 V (see Figure 12)	T_A = 25°C		0.25	0.5	
			T_A = –40°C to 85°C			0.6	
$I_{NO(OFF)}$, $I_{NC (OFF)}$	NO and NC OFF leakage current	V_{NO} = 0.5 V, 2.2 V, V_{COM} = 2.2 V, 0.5 V, V_{NC} = open, or V_{NC} = 0.5 V, 2.2 V, V_{COM} = 2.2 V, 0.5 V, V_{NO} = open, switch OFF, and V_{CC} = 2.75 V (see Figure 13)	T_A = 25°C	–20	2	20	nA
			T_A = –40°C to 85°C	–50		50	
$I_{NO(PWROFF)}$, $I_{NC (PWROFF)}$	NO and NC PWROFF leakage current	V_{NO} or V_{NC} = 0 V to 2.75 V, V_{COM} = 2.75 V to 0 V, switch OFF, and V_{CC} = 0 V (see Figure 13)	T_A = 25°C	–10		10	µA
			T_A = –40°C to 85°C	–10		10	
$I_{NO(ON)}$	NC and NO ON leakage current	V_{NO} = 0.5 V, 2.2 V, V_{NC} and V_{COM} = open, or V_{NC} = 2.2 V, 0.5 V, V_{NO} and V_{COM} = open, switch ON, and V_{CC} = 2.75 V (see Figure 14)	T_A = 25°C	–20	2	20	nA
			T_A = –40°C to 85°C	–100		100	
$I_{COM(ON)}$	COM ON leakage current	V_{COM} = 0.5 V, V_{NO} and V_{NC} = open, or V_{COM} = 2.2 V, V_{NO} and V_{NC} = open, switch ON, and V_{CC} = 2.75 V (see Figure 14)	T_A = 25°C	–20	2	20	nA
			T_A = –40°C to 85°C	–100		100	
$I_{COM(PWROFF)}$	COM OFF leakage current	V_{NO} or V_{NC} = 0 V to 2.75 V, V_{COM} = 2.75 V to 0 V, and V_{CC} = 0 V (see Figure 13)	T_A = 25°C	–10		10	µA
			T_A = –40°C to 85°C	–10		10	

(1) The algebraic convention (whereby the most negative value is a minimum and the most positive value is a maximum)

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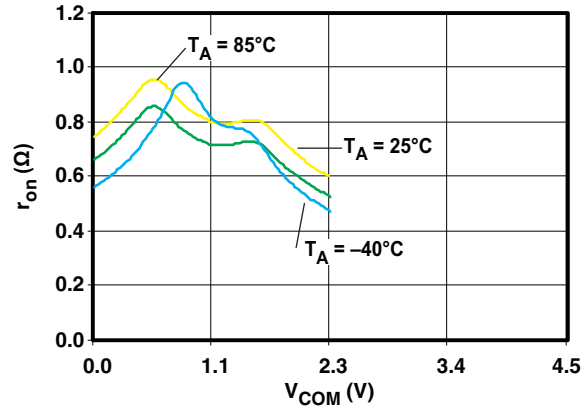
Electrical Characteristics – 2.5-V Supply (continued)

V_{CC} = 2.25 V to 2.75 V and T_A = –40°C to 85°C (unless otherwise noted)(1)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
DIGITAL CONTROL INPUT (IN)							
V_{IH}	Input logic high	V_{CC} = 2.75 V and T_A = –40°C to 85°C		1.05		5.5	V
V_{IL}	Input logic low	V_{CC} = 2.75 V and T_A = –40°C to 85°C		0		0.65	V
I_{IH}, I_{IL}	Input leakage current	V_{IN} = 1.95 V or 0, V_{CC} = 2.75 V, and T_A = –40°C to 85°C		–0.05		0.5	µA
r_{IN}	Input resistance	V_{IN} = 1.95 V, V_{CC} = 2.75 V, and T_A = –40°C to 85°C			6		MΩ
DYNAMIC							
t_{ON}	Turnon time	V_{COM} = V_{CC}, R_L = 50 Ω, and C_L= 35 pF (see Figure 16)	V_{CC} = 2.5 V and T_A = 25°C		97	170	ns
			V_{CC} = 2.25 V and T_A = –40°C to 85°C			175	
t_{OFF}	Turnoff time	V_{COM} = V_{CC}, R_L = 50 Ω, and C_L = 35 pF (see Figure 16)	V_{CC} = 2.5 V and T_A = 25°C		80	155	ns
			V_{CC} = 2.25 V and T_A = –40°C to 85°C			160	
t_{BBM}	Break-before-make time	V_{COM} = V_{CC} , R_L = 50 Ω, and C_L = 35 pF (see Figure 17)	V_{CC} = 2.5 V and T_A = 25°C	5	18	35	ns
			V_{CC} = 2.25 V and T_A = –40°C to 85°C	5		40	
Q_C	Charge injection	V_{GEN} = 0, R_{GEN} = 0, C_L = 1 nF, V_{CC} = 2.5 V, and T_A = 25°C (see Figure 21)			82		pC
$C_{NO(OFF)}$	NO OFF capacitance	V_{NO} = V_{CC} or GND, switch OFF, V_{CC} = 2.5 V, and T_A = 25°C (see Figure 15)			29		pF
$C_{NC(ON)}$, $C_{NO(ON)}$	NC and NO ON capacitance	V_{NC} or V_{NO} = V_{CC} or GND, switch ON, V_{CC} = 2.5 V, and T_A = 25°C (see Figure 15)			116		pF
$C_{COM(ON)}$	COM ON capacitance	V_{COM} = V_{CC} or GND, switch ON, V_{CC} = 2.5 V, and T_A = 25°C (see Figure 15)			116		pF
C_I	Digital input capacitance	V_{IN} = V_{CC} or GND, V_{CC} = 2.5 V, and T_A = 25°C (see Figure 15)			3		pF
BW	Bandwidth	R_L = 50 Ω, switch ON, V_{CC} = 2.5 V, and T_A = 25°C (see Figure 18)			54		MHz
O_{ISO}	OFF isolation	R_L = 50 Ω, f = 1 MHz, V_{CC} = 2.5 V, and T_A = 25°C (see Figure 19)			–63		dB
X_{TALK}	Crosstalk	R_L = 50 Ω, f = 1 MHz, V_{CC} = 2.5 V, and T_A = 25°C (see Figure 20)			–63		dB
THD	Total harmonic distortion	R_L = 600 Ω, C_L = 50 pF, V_{CC} = 2.5 V, f = 20 Hz to 20 kHz, and T_A = 25°C (see Figure 22)			0.008%		
SUPPLY							
ICC	Positive supply current	V_{IN} = 1.95 V or GND, V_{CC} = 2.75 V, and T_A = –40°C to 85°C				10	µA

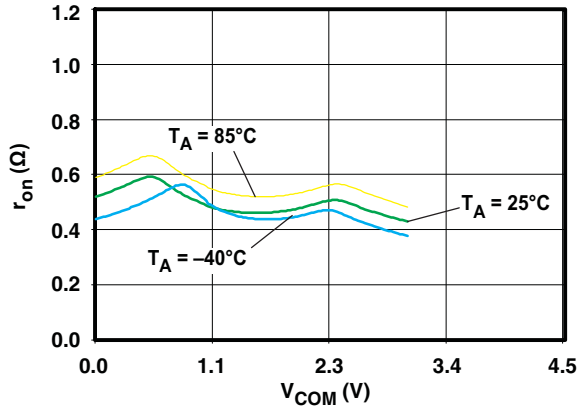
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6.8 Typical Characteristics



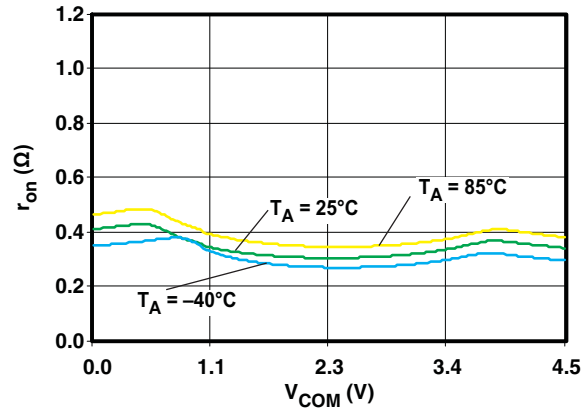
(V_{CC} = 2.25 V)

Figure 1. r_{on} vs V_{COM}



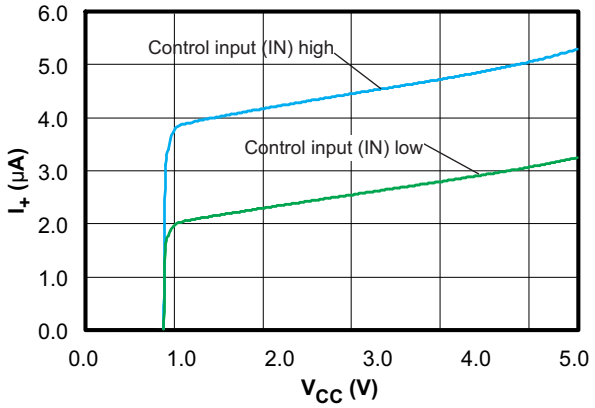
(V_{CC} = 3 V)

Figure 2. r_{on} vs V_{COM}



(V_{CC} = 4.5 V)

Figure 3. r_{on} vs V_{COM}



(T_A = 25°C)

Figure 4. I_{CC} vs V_{CC}

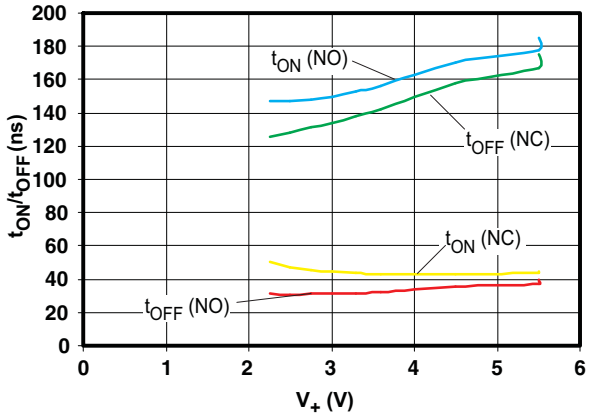


Figure 5. t_{ON}/t_{OFF} vs Supply Voltage

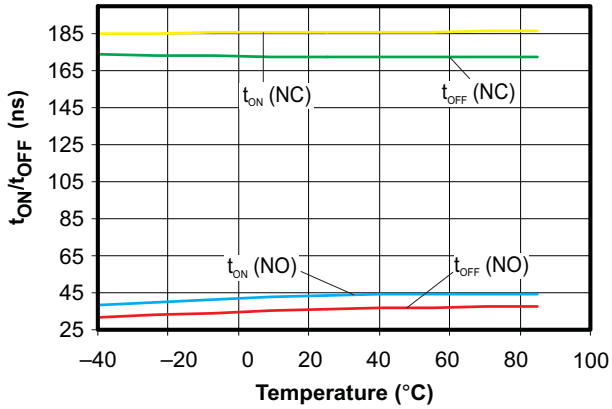


Figure 6. t_{ON}/t_{OFF} vs Temperature

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Typical Characteristics (continued)

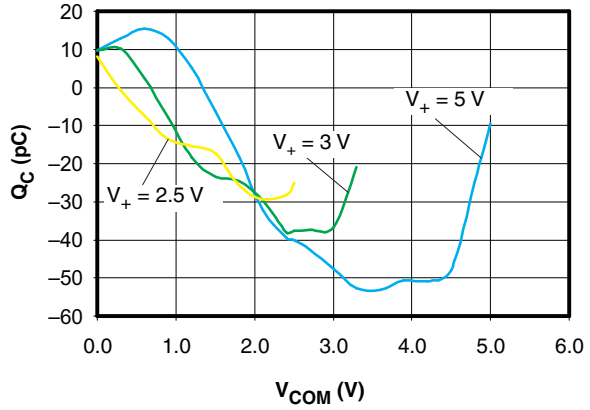


Figure 7. Charge Injection (Q_C) vs V_{COM}

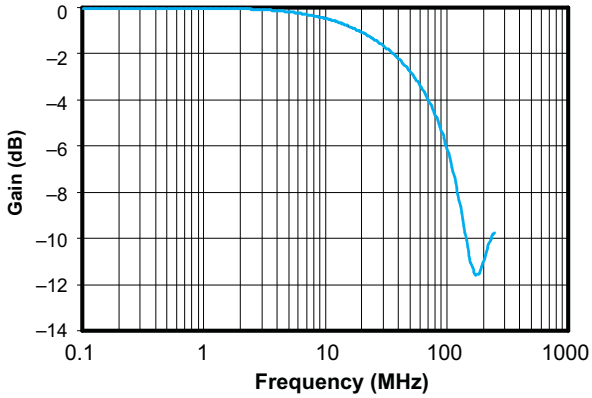


Figure 8. Gain vs Frequency

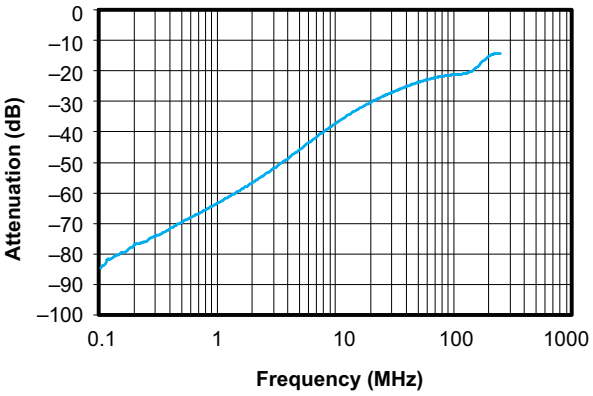


Figure 9. OFF Isolation vs Frequency

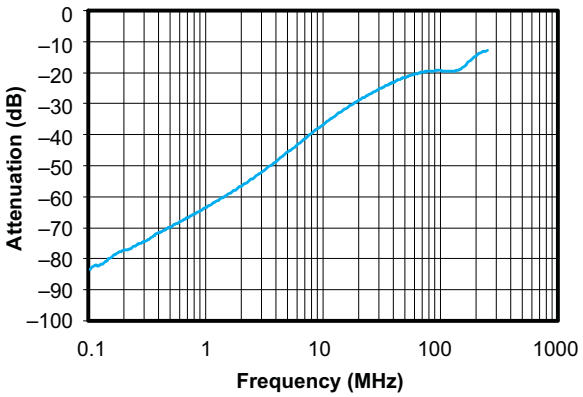


Figure 10. Crosstalk vs Frequency

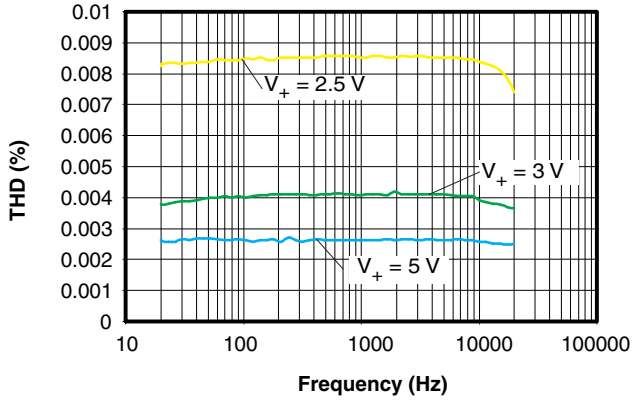


Figure 11. Total Harmonic Distortion (THD) vs Frequency

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7 Parameter Measurement Information

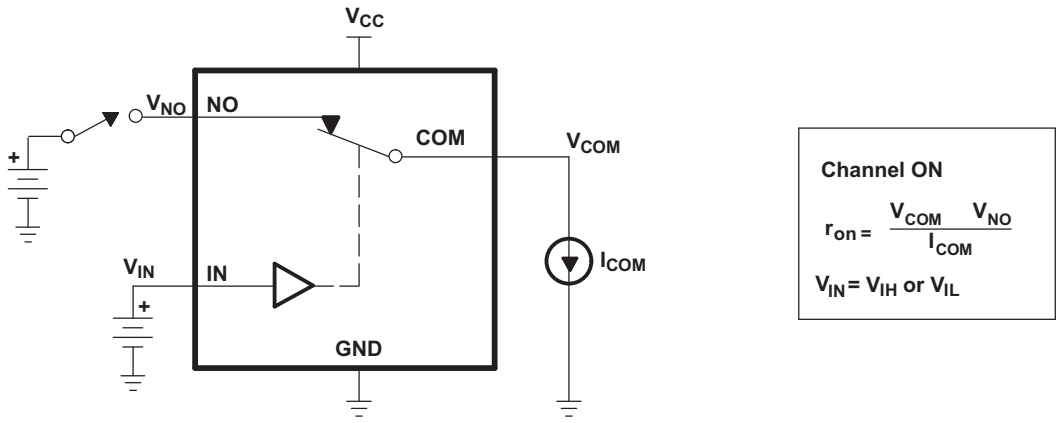


Figure 12. ON-State Resistance (r_{on})

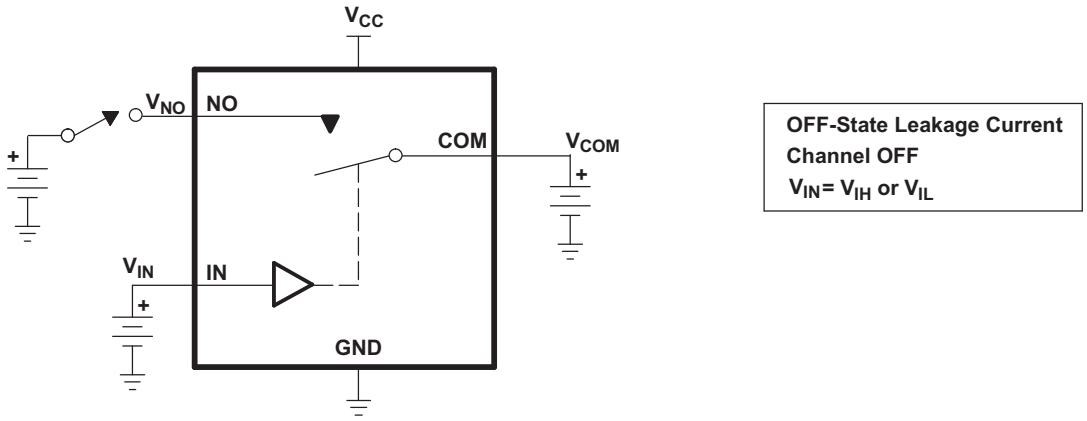


Figure 13. OFF-State Leakage Current ($I_{COM(OFF)}$, $I_{NC(OFF)}$, $I_{COM(PWROFF)}$, $I_{NC(PWR(FF)}$)

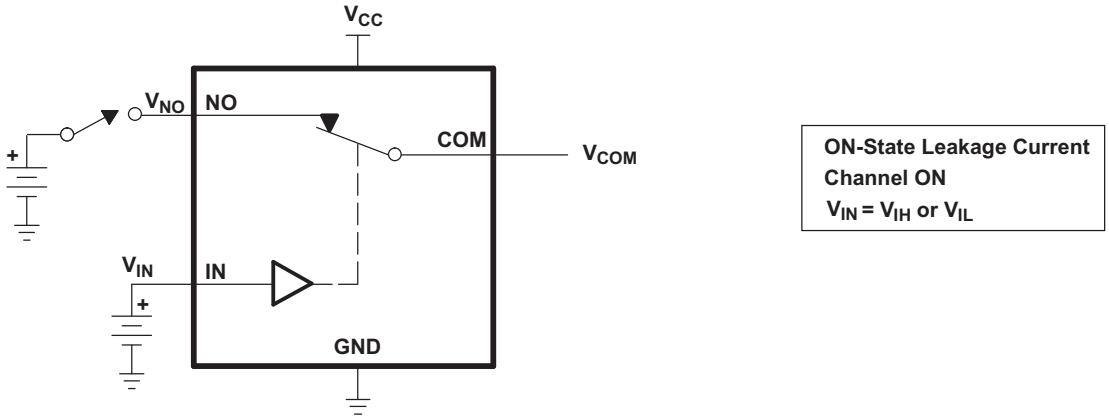


Figure 14. ON-State Leakage Current ($I_{COM(ON)}$, $I_{NC(ON)}$)

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Parameter Measurement Information (continued)

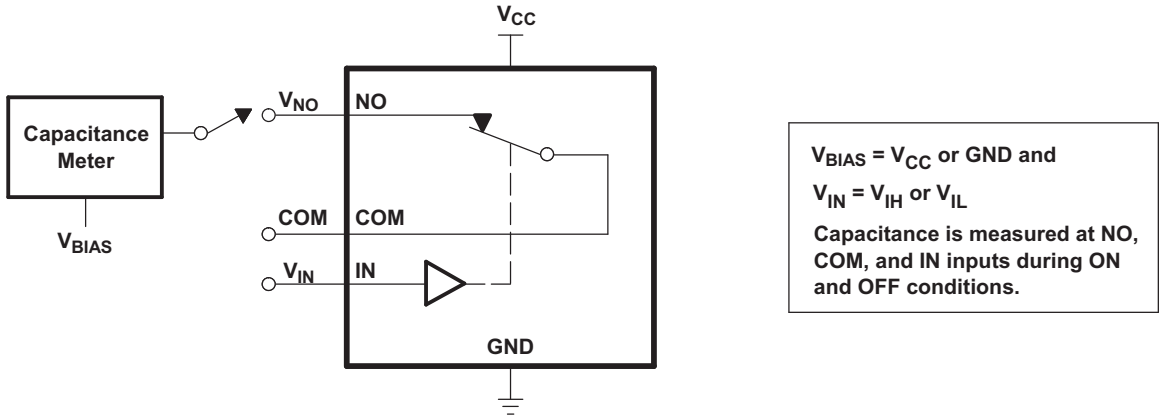
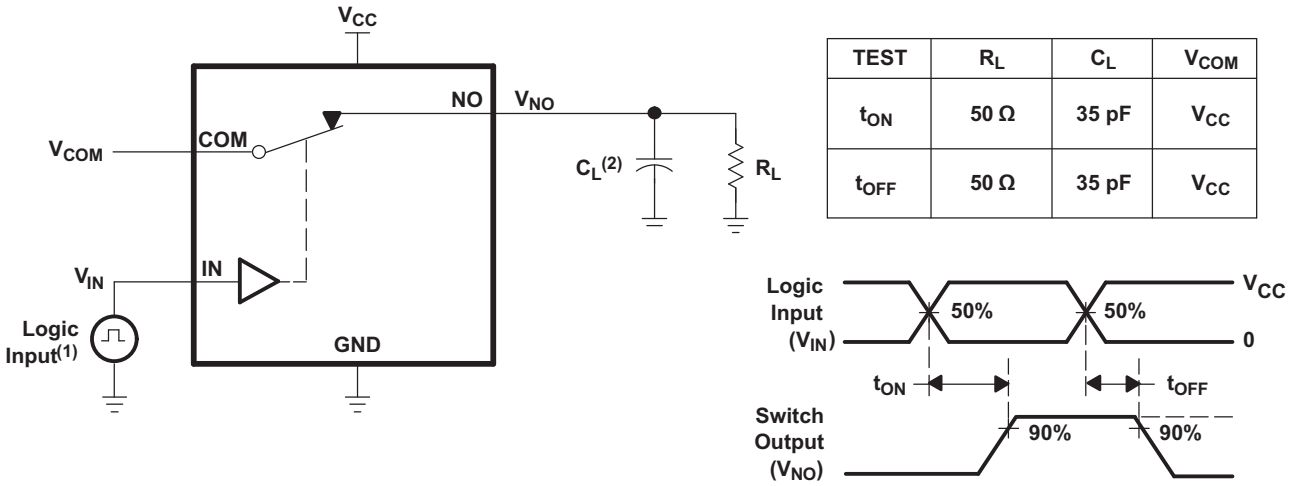


Figure 15. Capacitance (C_I, $C_{COM(OFF)}$, $C_{COM(ON)}$, $C_{NC(OFF)}$, $C_{NC(ON)}$)



TEST	R_L	C_L	V_{COM}
t_{ON}	50 Ω	35 pF	V_{CC}
t_{OFF}	50 Ω	35 pF	V_{CC}

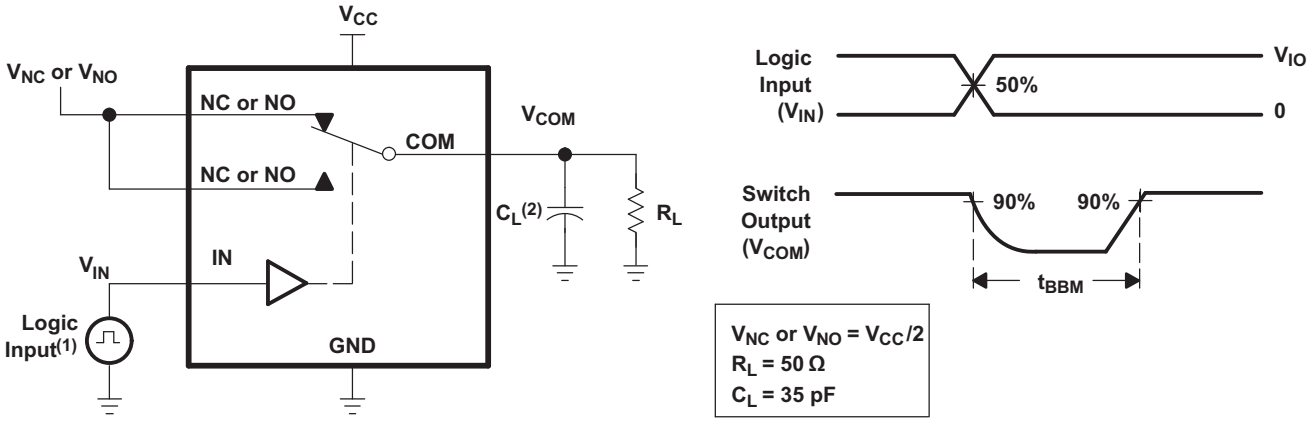
A. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r < 5 ns, t_f < 5 ns.

B. C_L includes probe and jig capacitance.

Figure 16. Turnon (t_{ON}) and Turnoff Time (t_{OFF})

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Parameter Measurement Information (continued)



A. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r < 5 ns, t_f < 5 ns.

B. C_L includes probe and jig capacitance.

Figure 17. Break-Before-Make Time (t_{BBM})

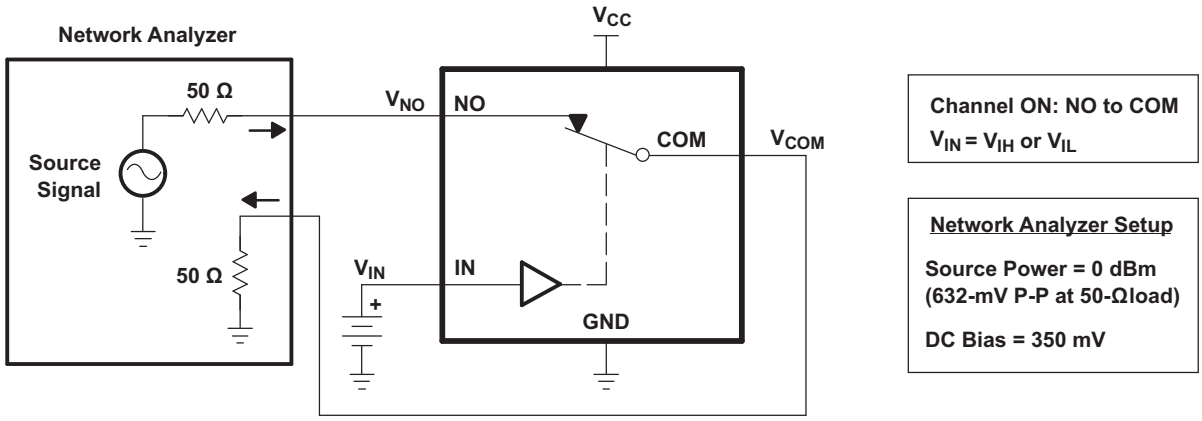


Figure 18. Bandwidth (BW)

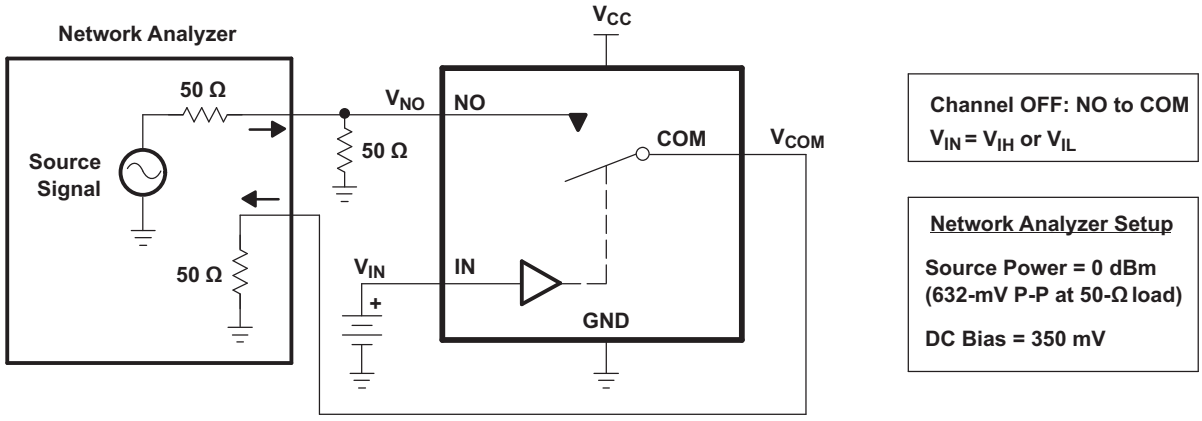


Figure 19. OFF Isolation (O_{ISO})

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Parameter Measurement Information (continued)

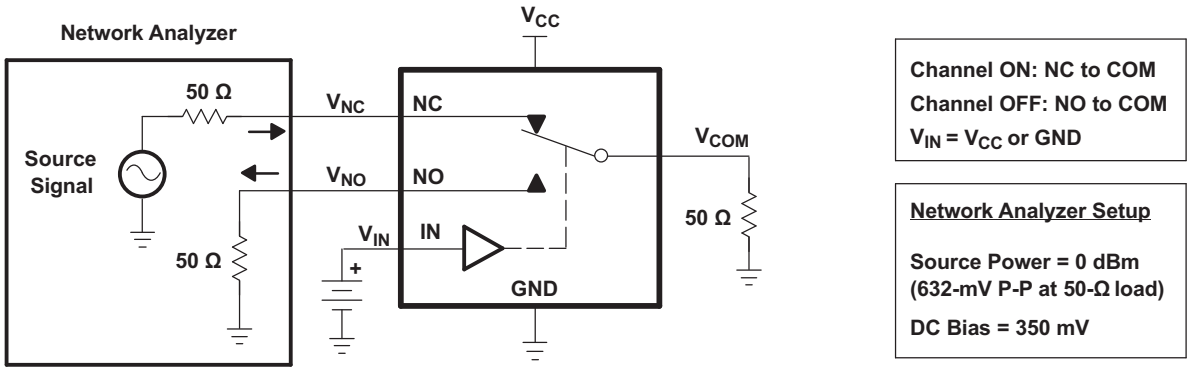
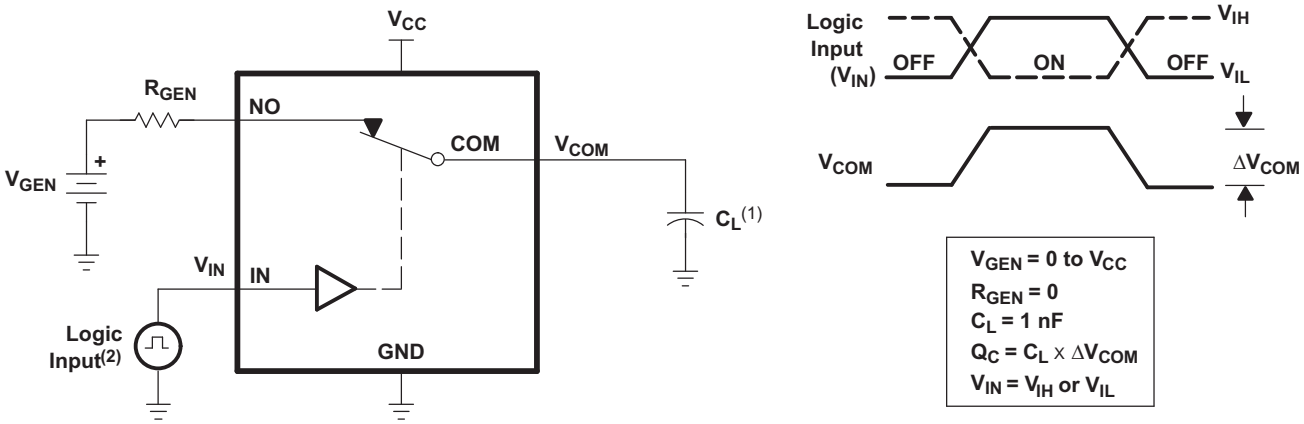


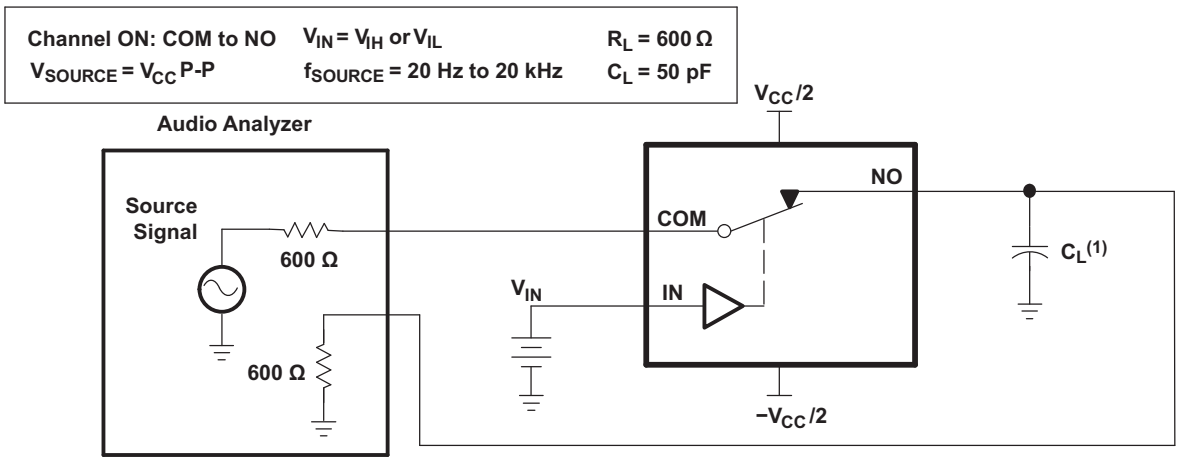
Figure 20. Crosstalk (X_{TALK})



A. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r < 5 ns, t_f < 5 ns.

B. C_L includes probe and jig capacitance.

Figure 21. Charge Injection (Q_C)



A. C_L includes probe and jig capacitance.

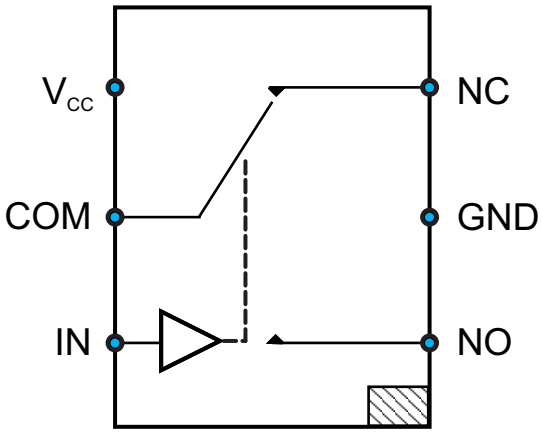
Figure 22. Total Harmonic Distortion (THD)

8 Detailed Description

8.1 Overview

The TS5A12301E device is a bidirectional, 1-channel, 1:2 mux, or single-pole double-throw (SPDT) analog switch. This switch offers low ON-state resistance and excellent THD performance, which makes it great for interfacing with an ADC.

8.2 Functional Block Diagram



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8.3 Feature Description

8.3.1 Isolation

Isolation in power-down mode prevents current leakage through the device's signal path when V_{CC} = 0 V. This allows signals to be present on the COM, NO, or NC pins before the device is powered up without damaging the device.

8.3.2 1.8-V Compatible Logic

The TS5A12301E supports 1.8-V logic irrespective to the supply voltage applied to the IC.

8.3.3 Integrated Control Input Pulldown

There is an integrated 6-MΩ pulldown resistor on the digital control input pin (IN) to keep the device in a known logic state during power up without needing an external component.

8.4 Device Functional Modes

Table 1 lists the functional modes of the TS5A12301E.

Table 1. Function Table

IN	NC TO COM, COM TO NC	NO TO COM, COM TO NO
L or Open	ON	OFF
H	OFF	ON

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9 Application and Implementation

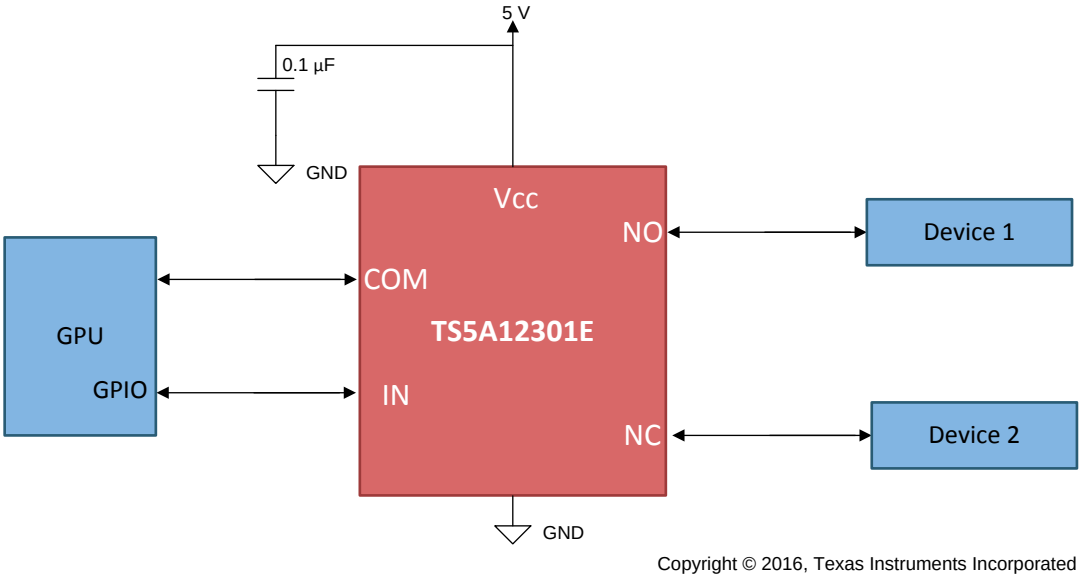
NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The switch is bidirectional, so the NO, NC, and COM pins may be used as either inputs or outputs.

9.2 Typical Application



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Figure 23. Application Schematic

9.2.1 Design Requirements

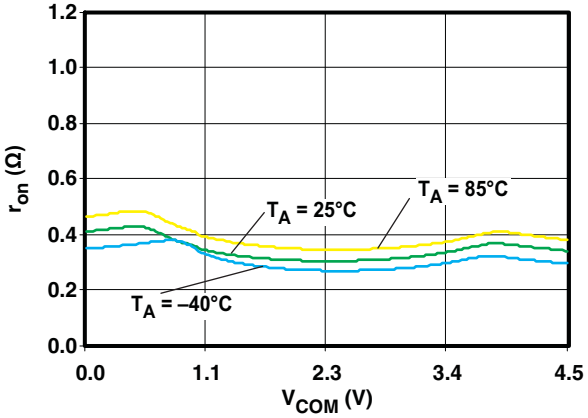
This TS5A12301E application may be properly operated without any external components. Unused pins (for example, COM, NC, and NO) may be left floating. Digital control pin (IN) has an integrated 6-MΩ pulldown resistor, so no external component is required to keep the logic pin in a known state.

9.2.2 Detailed Design Procedure

To ensure proper performance, keep all signals passing through the switch within the ranges specified in *Recommended Operating Conditions*.

Typical Application (continued)

9.2.3 Application Curve



V_{CC} = 4.5 V

Figure 24. r_{on} vs V_{COM}

10 Power Supply Recommendations

The TS5A12301E does not have power sequencing requirements. If there is a voltage present on the COM, NC, and NO pins before power is supplied to the VCC pin, the isolation feature in power-down mode (V_{CC} = 0) protects the device and signal path.

Although it is not required, power-supply bypassing improves noise margin and prevents switching noise propagation from the VCC supply to other components. A 0.1-µF capacitor, connected from VCC to GND, is adequate for most applications.

11 Layout

11.1 Layout Guidelines

High-speed switches require proper layout and design procedures for optimum performance. Reduce stray inductance and capacitance by keeping traces short and wide. Ensure that bypass capacitors are placed as close to the device as possible. Use large ground planes where possible.

11.2 Layout Example

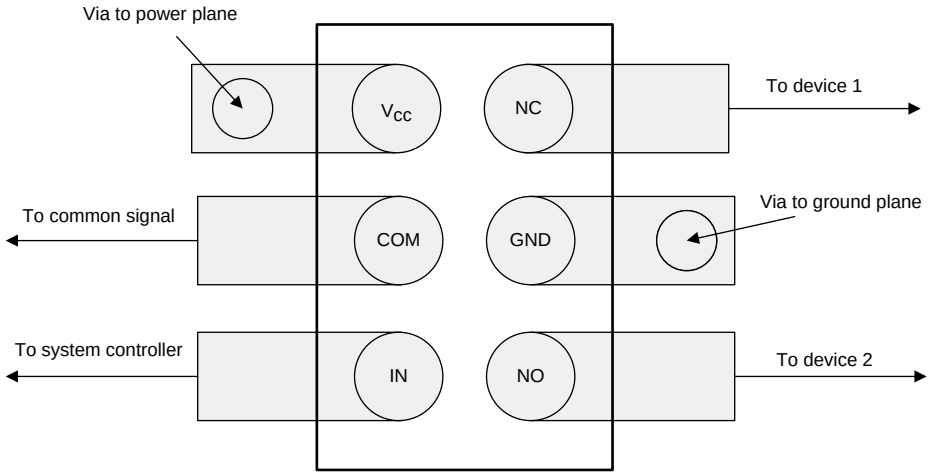


Figure 25. TS5A12301E Layout

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12 Device and Documentation Support

12.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community ***TI's Engineer-to-Engineer (E2E) Community.*** Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support ***TI's Design Support*** Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.3 Trademarks

E2E is a trademark of Texas Instruments.
All other trademarks are the property of their respective owners.

12.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.5 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TS5A12301EYFPR	ACTIVE	DSBGA	YFP	6	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(3W2 ~ 3W7 ~ 3WN)	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

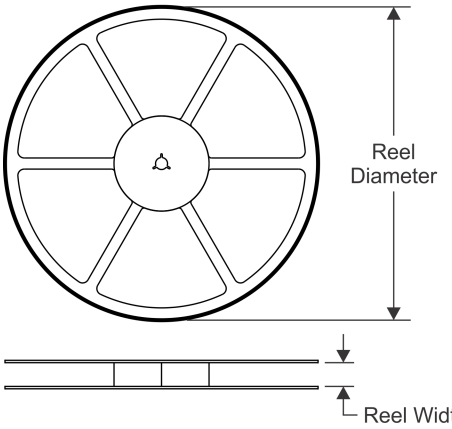
(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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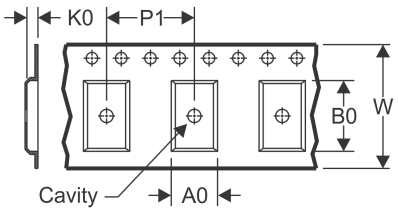
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TAPE AND REEL INFORMATION

REEL DIMENSIONS

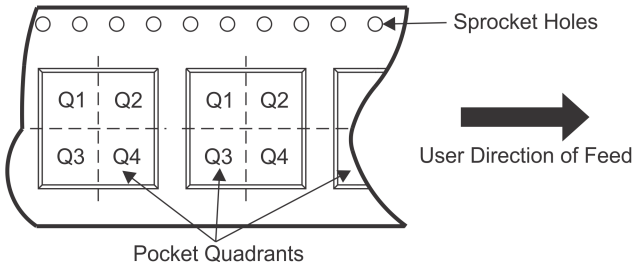


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

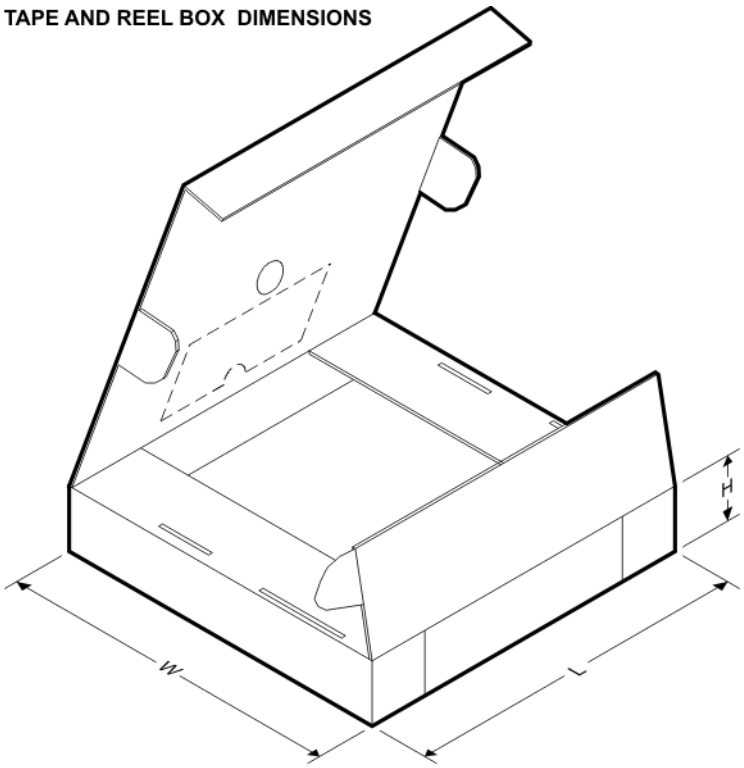
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS5A12301EYFPR	DSBGA	YFP	6	3000	178.0	9.2	0.89	1.29	0.62	4.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

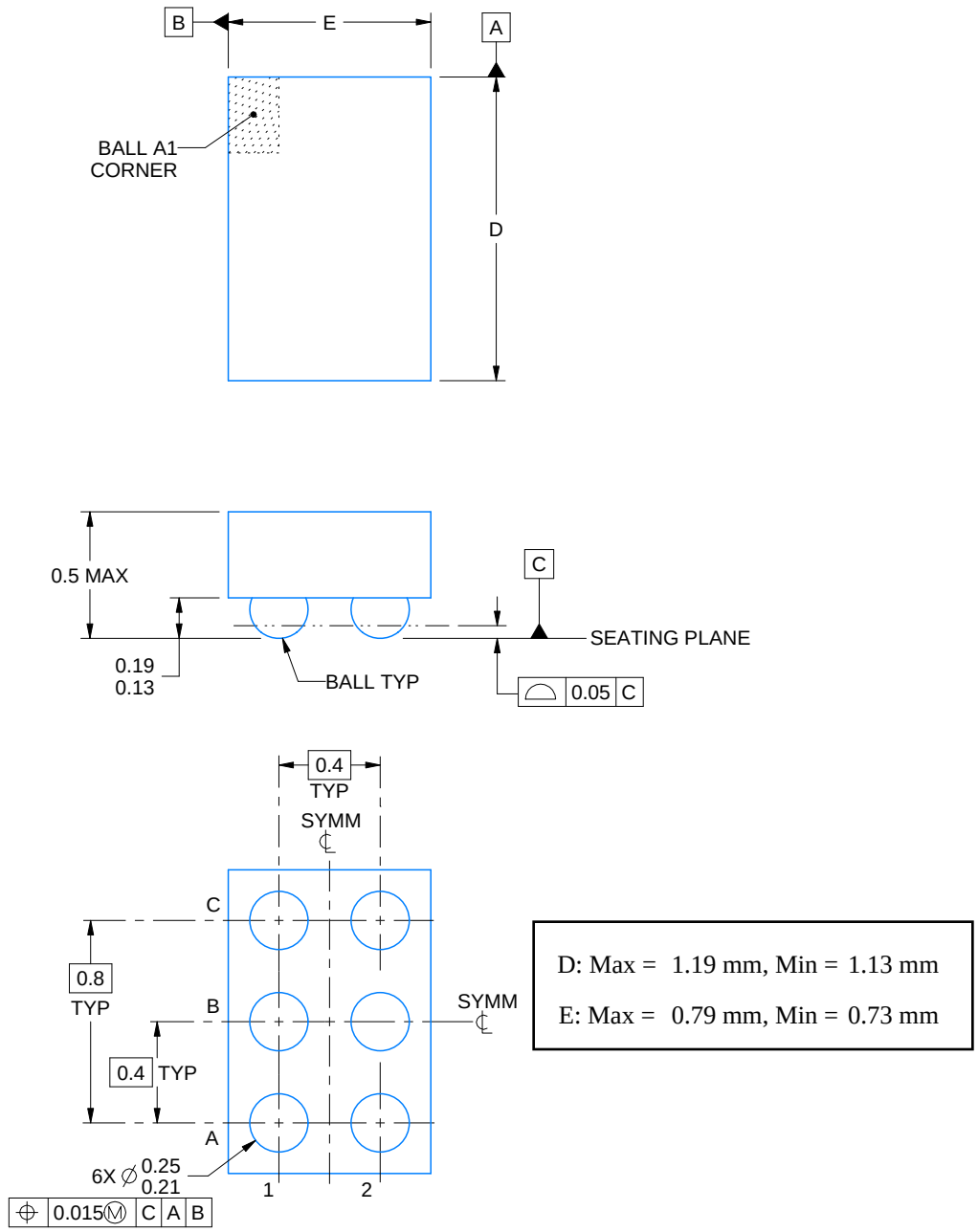
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS5A12301EYFPR	DSBGA	YFP	6	3000	220.0	220.0	35.0

PACKAGE OUTLINE

YFP0006

DSBGA - 0.5 mm max height

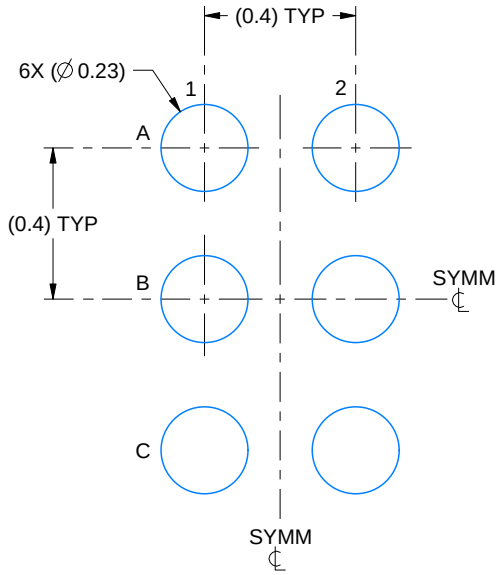
DIE SIZE BALL GRID ARRAY



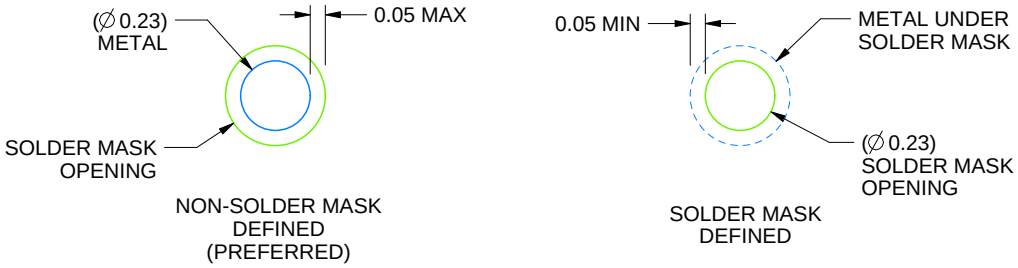
4223410/A 11/2016

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.



LAND PATTERN EXAMPLE
SCALE:50X

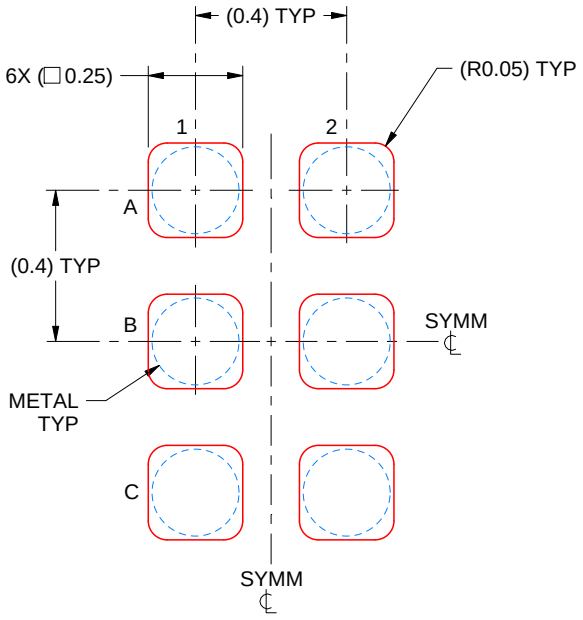


SOLDER MASK DETAILS
NOT TO SCALE

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NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints.
   For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICK STENCIL
SCALE:50X

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NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

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